



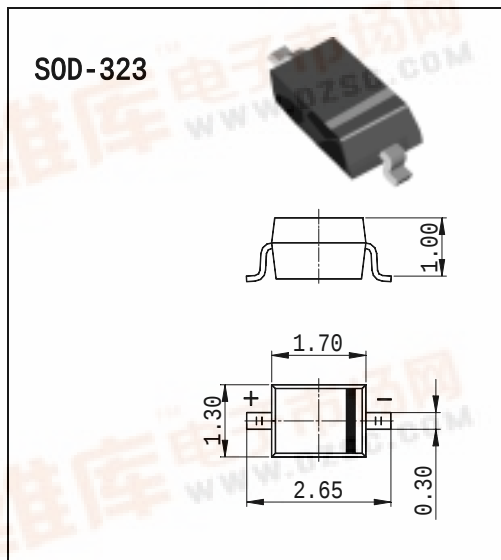
查询BAS40WS-SOD-323供应商

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JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOD-323 Plastic-Encapsulate Diode

- Low Turn-on Voltage
- Fast Switching
- PN Junction Guard Ring for Transient and ESD Protection



Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	BAS40	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	40	V
Forward Continuous Current (Note 1)	I_{FM}	200	mA
Power Dissipation (Note 1)	P_d	350	mW
Forward Surge Current (Note 1) @ $t < 1.0\text{s}$	I_{FSM}	600	mA
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Operating Junction Temperature Range	T_j	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-65 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

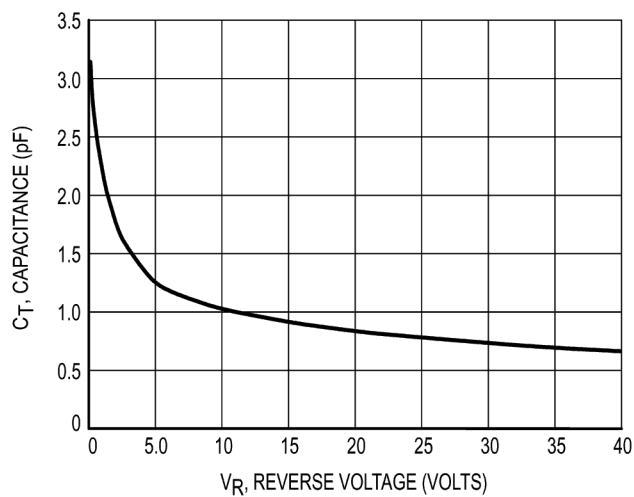
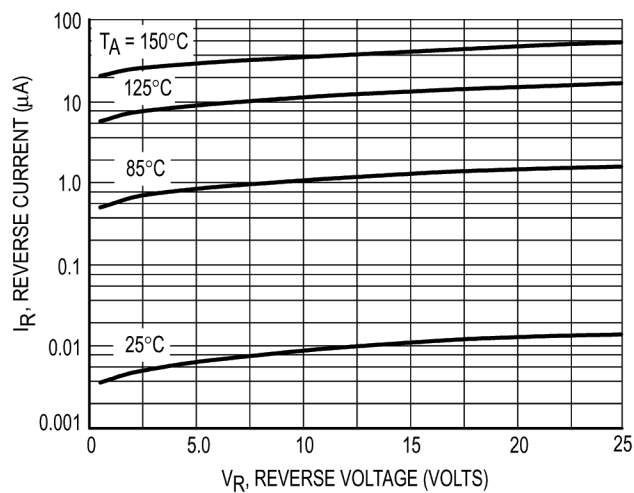
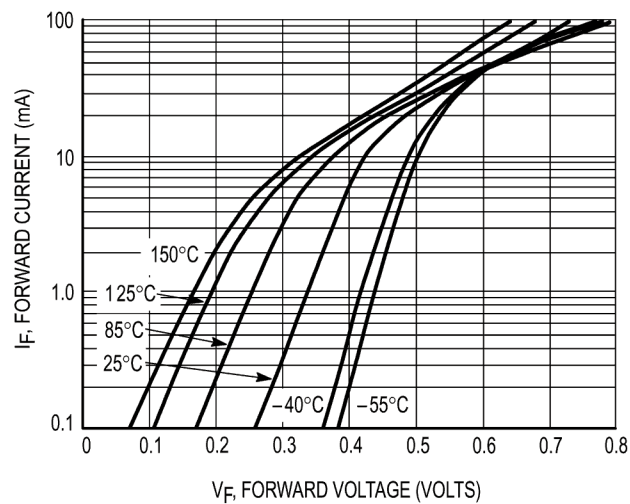
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Breakdown Voltage	$V_{(BR)R}$	40	—	—	V	$I_R = 10\mu\text{A}$
Forward Voltage	V_F	—	—	380 1000	mV	$t_p < 300\mu\text{s}$, $I_F = 1.0\text{mA}$ $t_p < 300\mu\text{s}$, $I_F = 40\text{mA}$
Reverse Leakage Current	I_R	—	20	200	nA	$t_p < 300\mu\text{s}$, $V_R = 30\text{V}$
Junction Capacitance	C_j	—	4.0	5.0	pF	$V_R = 0\text{V}$, $f = 1.0\text{MHz}$
Reverse Recovery Time	t_{rr}	—	—	5.0	ns	$I_F = I_R = 10\text{mA}$ to $I_R = 1.0\text{mA}$, $R_L = 100\Omega$

Notes: 1. Valid Provided that terminals are kept at ambient temperature.

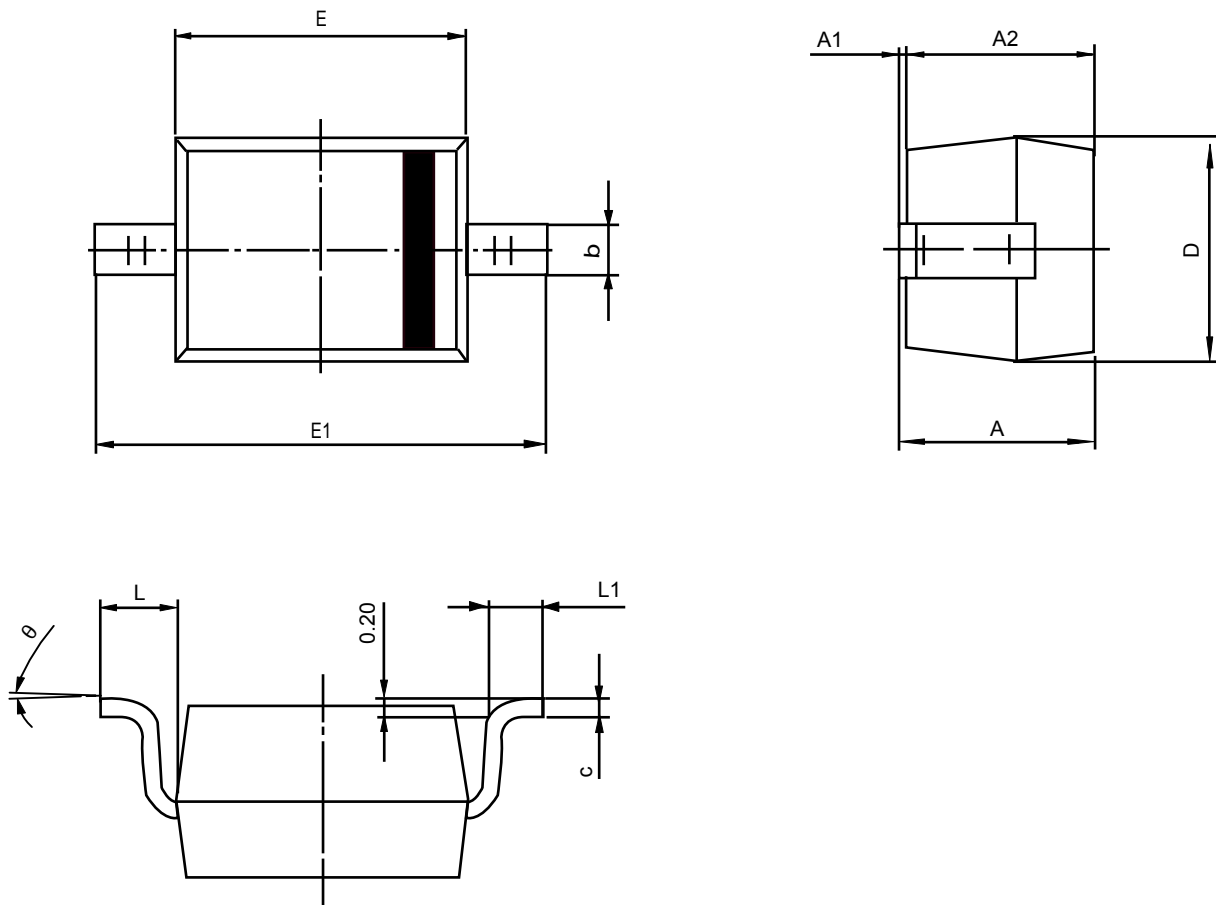


Typical Characteristics

BAS40WS



SOD-323 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.500	2.800	0.098	0.110
L	0.475REF		0.019REF	
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°